

isc Silicon NPN Power Transistor

2SC6011/A

DESCRIPTION

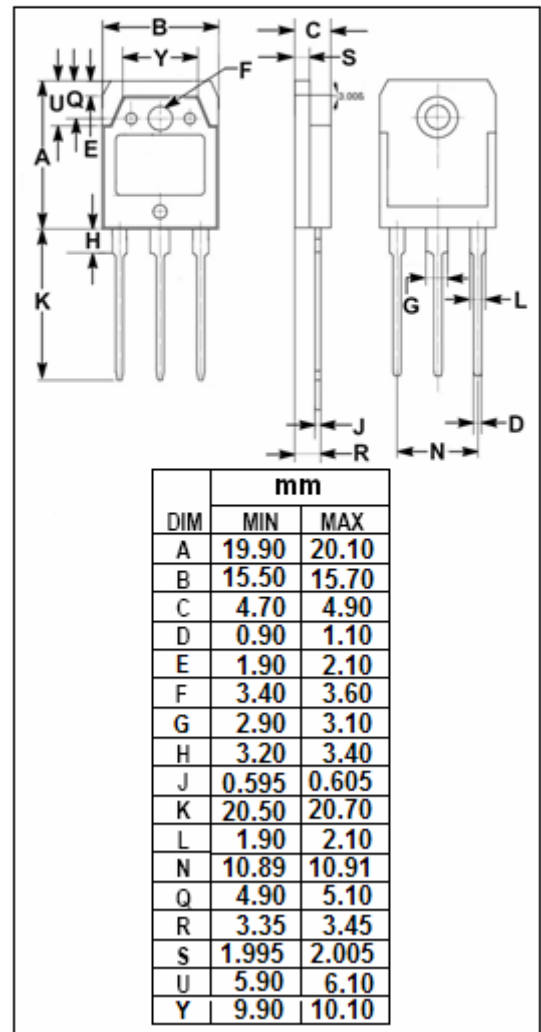
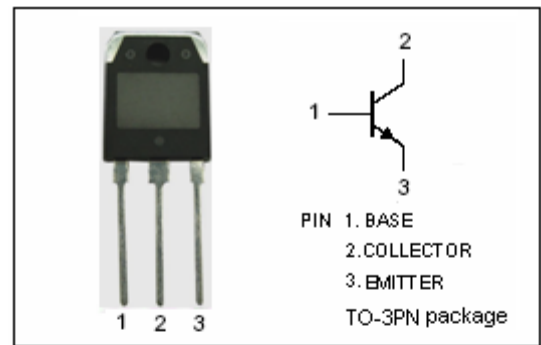
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 200V(\text{Min})-2SC6011$   
=  $200V(\text{Min})-2SC6011A$
- Good Linearity of  $h_{FE}$
- Complement to Type 2SA2151/A

APPLICATIONS

- Designed for audio and general purpose applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
$V_{CBO}$	Collector-Base Voltage	2SC6011	200	V
		2SC6011A	230	
$V_{CEO}$	Collector-Emitter Voltage	2SC6011	200	V
		2SC6011A	230	
$V_{EBO}$	Emitter-Base Voltage	6	V	
$I_C$	Collector Current-Continuous	15	A	
$I_B$	Base Current-Continuous	4	A	
$P_C$	Collector Power Dissipation @ $T_C=25^\circ C$	160	W	
$T_J$	Junction Temperature	150	°C	
$T_{stg}$	Storage Temperature Range	-55~150	°C	



**isc Silicon NPN Power Transistor****2SC6011/A****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	2SC6011	$I_C=50\text{mA}; I_B=0$	200			V
		2SC6011A		230			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		$I_C=5\text{A}; I_B=0.5\text{A}$			0.5	V
$I_{CBO}$	Collector Cutoff Current	2SC6011	$V_{CB}=200\text{V}; I_E=0$			10	$\mu\text{A}$
		2SC6011A	$V_{CB}=230\text{V}; I_E=0$				
$I_{EBO}$	Emitter Cutoff Current		$V_{EB}=6\text{V}; I_C=0$			10	$\mu\text{A}$
$h_{FE}$	DC Current Gain		$I_C=3\text{A}; V_{CE}=4\text{V}$	50		180	
$C_{OB}$	Output Capacitance		$I_E=0; V_{CB}=10\text{V}; f_{test}=1.0\text{MHz}$		270		pF
$f_T$	Current-Gain—Bandwidth Product		$I_E=-0.5\text{A}; V_{CE}=12\text{V}$		20		MHz

◆  **$h_{FE}$  Classifications**

O	P	Y
50-100	70-140	90-180